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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Attorney Docket Number	23-65037-09		
Application Number	10/581,281		
Filing Date	May 31, 2006		
First Named Inventor	Larry C. Olsen		
Art Unit	1795		
Examiner Name	Shannon M. Gardner		

## U.S. PATENT DOCUMENTS

Copies of U.S. Patent documents do not need to be provided, unless requested by the Patent and Trademark Office. For patents, provide the patent number and the issue date. For published U.S. applications, provide the publication number and the publication date. For unpublished pending patent applications, provide the application number and the filing date and submit a copy.

Examiner's Initials*	Cite No. (optional)	Number	Date	Name of Applicant or Patentee
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## FOREIGN PATENT DOCUMENTS Country Number Date Name of Applicant or Patentee

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<sup>\*</sup> Examiner: Initial if reference considered, whether or not in conformance with MPEP 609. Draw line through cite if not in conformance and not considered. Include copy of this form with next communication to applicant.